

21 Jan '02

Dear Linda:

Fred would have preferred me to email my viewgraphs but they were in a number of different formats, so I decided to mail you copies instead.

Dave Aspnes

SIMPLIFIED BOND HYPERPOLARIZABILITY MODEL OF
SECOND-HARMONIC GENERATION:
APPLICATION TO Si-DIELECTRIC INTERFACES

J.-F. T. WANG
G. D. POWELL, R. S. JOHNSON, G. LUCOVSKY, AND
D. E. ASPNES

Physics Department, NC State University, Raleigh, NC 27695-8202

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MOTIVATION:

- Better understand the atomic and electronic structure of Si-dielectric interfaces
- Better understand the origins of linear and nonlinear optical responses of interfaces
- Better control of interface properties
- Improve accuracy of thin-film metrology and optical characterization of interfaces

LINEAR AND NONLINEAR OPTICS:

Interaction energy:

$$H' = q\phi_0 - \vec{p} \cdot \vec{E} - \vec{m} \cdot \vec{B} - \sum Q_{ij} \frac{\partial E_i}{\partial x_j} - \dots$$

At high fields:

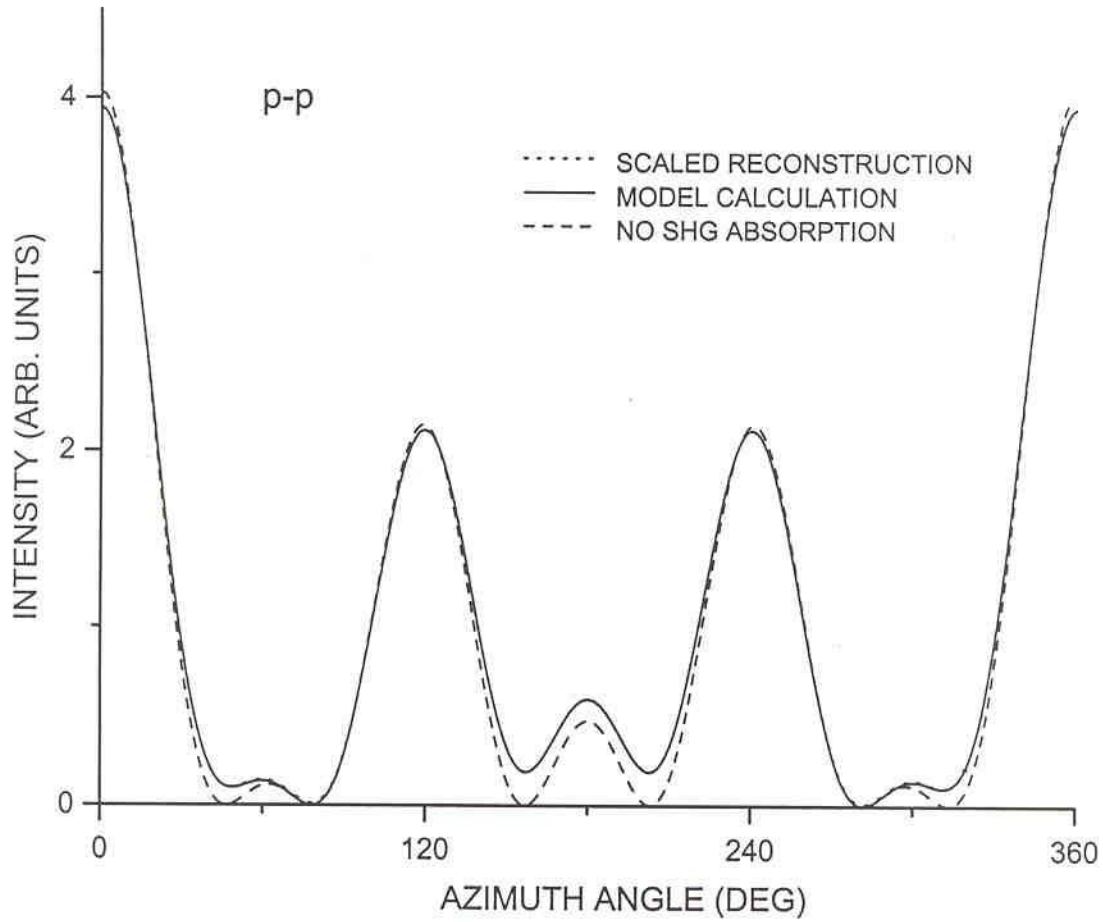
$$P_i = \chi_i^{(1)} E_j + \chi_{ijk}^{(2)} E_j E_k + \chi_{ijkl} E_j E_k E_l + \dots$$

SHG:

Spectra still difficult to obtain, therefore SHG typically studied as anisotropies (dependences of $I^{(2)}(\phi)$ as a function of sample azimuth ϕ)

Classical methods of analysis:

1. As symmetry-allowed components of $\chi^{(2)}$
[No microscopic insight]
2. As Fourier coefficients of $I^{(2)}(\phi)$
[No microscopic insight]
3. By first-principles band structure calculations
[Arcane, physical insight not easy to obtain]



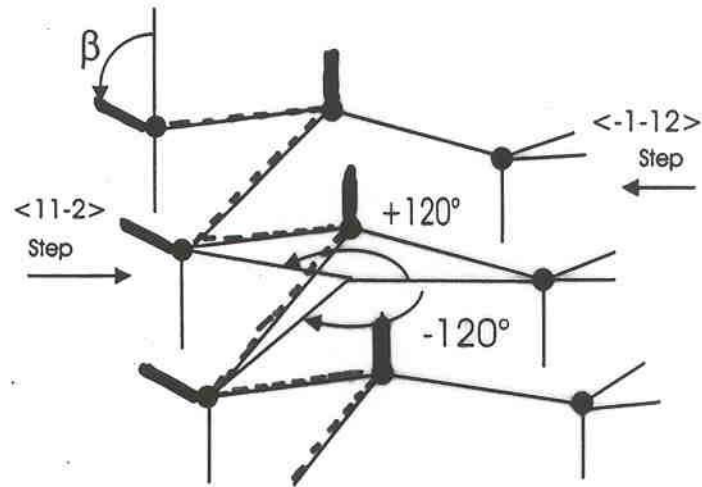


Figure 4.7: Geometry of interface bonds for vicinal (111) Si.

Bond vectors:

$$\hat{b}_1 = \frac{1}{\sqrt{3}} (\hat{x} + \hat{y} + \hat{z})$$

$$\hat{b}_2 = \frac{1}{\sqrt{3}} (\hat{x} - \hat{y} - \hat{z})$$

$$\hat{b}_3 = \frac{1}{\sqrt{3}} (-\hat{x} + \hat{y} - \hat{z})$$

$$\hat{b}_4 = \frac{1}{\sqrt{3}} (-\hat{x} - \hat{y} + \hat{z})$$

Simple model of electric-dipole second-harmonic generation from interfaces

Michele Cini

Dipartimento di Fisica, II Università degli Studi di Roma, Via Orazio Raimondo 00173 Roma, Italy

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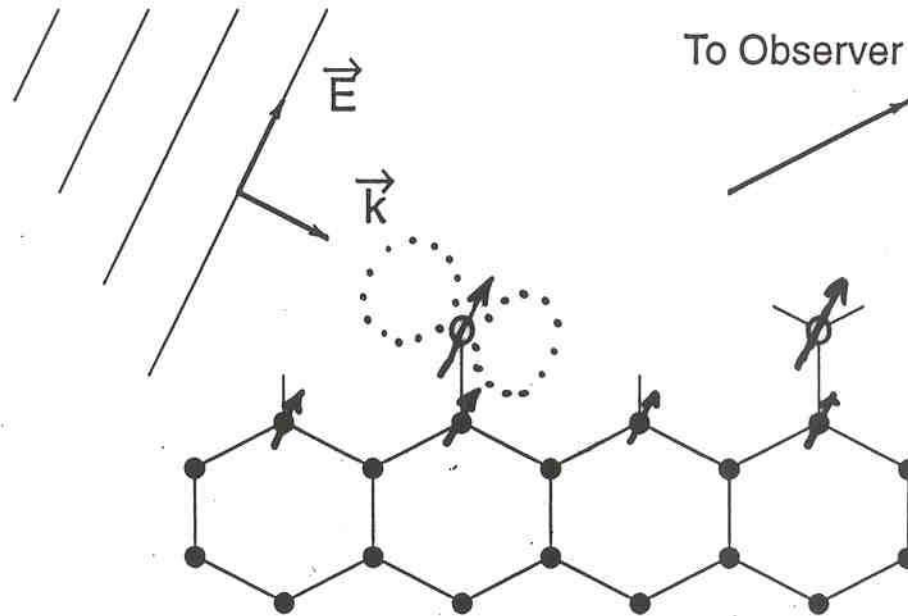
$$\begin{aligned}
X(\omega_1, \omega_2) = & \sum_s f(s) \sum_n [1-f(n)] \sum_r [1-f(r)] \left(\frac{[V_E(\omega_3)]_{sn} [V_A(\omega_2)]_{nr} [V_A(\omega_1)]_{rs}}{(\omega_{rs} - \omega_1 - i0)(\omega_{ns} - \omega_1 - \omega_2 - i0)} + \frac{[V_A(\omega_2)]_{sn} [V_E(\omega_3)]_{nr} [V_A(\omega_1)]_{rs}}{(\omega_{rs} - \omega_1 - i0)(\omega_3 - \omega_1 + \omega_{ns} - i0)} \right. \\
& \left. + \frac{[V_A(\omega_2)]_{sn} [V_A(\omega_1)]_{nr} [V_E(\omega_3)]_{rs}}{(\omega_3 + \omega_{rs} - i0)(\omega_3 - \omega_1 + \omega_{ns} - i0)} \right) \\
& - \sum_s f(s) \sum_n [1-f(n)] \sum_m f(m) \left(\frac{[V_E(\omega_3)]_{mn} [V_A(\omega_2)]_{sm} [V_A(\omega_1)]_{ns}}{(\omega_{ns} - \omega_1 - i0)(\omega_{nm} - \omega_1 - \omega_2 - i0)} \right. \\
& \left. + \frac{[V_A(\omega_2)]_{mn} [V_E(\omega_3)]_{sm} [V_A(\omega_1)]_{ns}}{(\omega_{ns} - \omega_1 - i0)(\omega_3 - \omega_1 - \omega_{mn} - i0)} + \frac{[V_A(\omega_2)]_{mn} [V_A(\omega_1)]_{sm} [V_E(\omega_3)]_{ns}}{(\omega_3 + \omega_{ns} - i0)(\omega_3 - \omega_1 - \omega_{mn} - i0)} \right)
\end{aligned}$$

(3)

OBSERVATION:

Because SHG from Si-dielectric interfaces originates from within several monolayers of the interface...
...why not use a bond model?

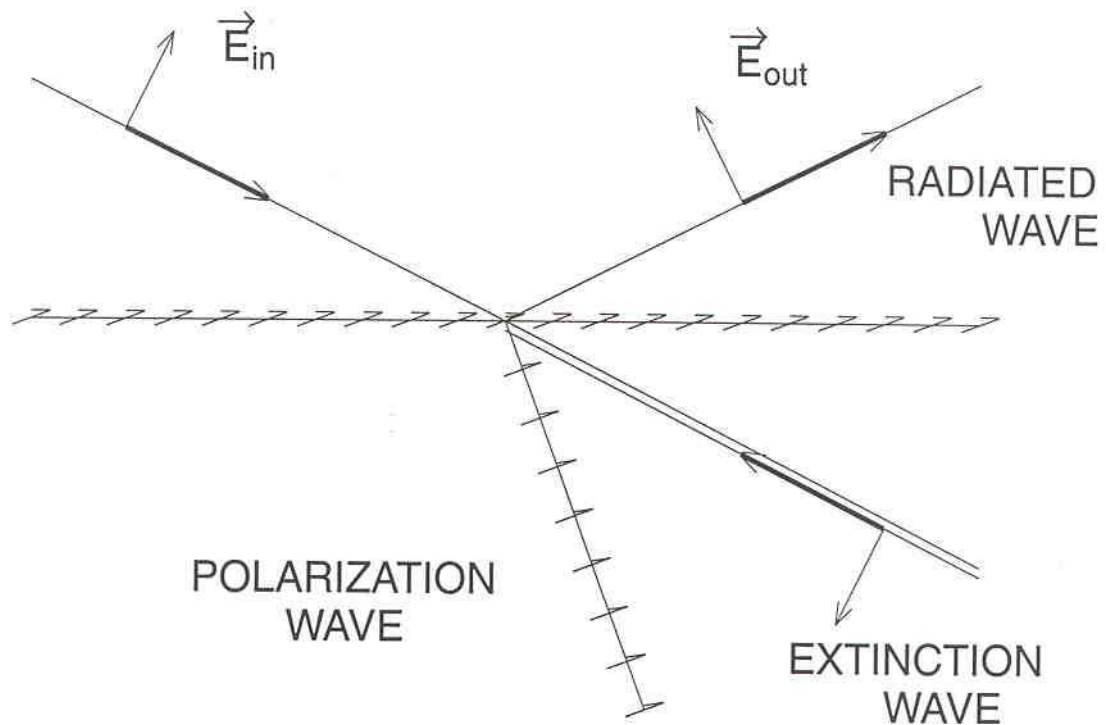
INTERACTION OF LIGHT WITH MATERIALS:



Radiation Zone:

$$\vec{E} = \frac{k^2}{r} e^{i\vec{k}r - i\omega t} \sum_n [\vec{p}_n - \hat{k}(\hat{k} \cdot \vec{p}_n)] e^{i(\vec{k}_i - \vec{k}_f) \cdot \vec{R}_n}$$

EWALD-OSEEN EXTINCTION THEOREM



$$\vec{\mathbf{F}} = m \vec{\mathbf{a}}$$

GENERAL FORCE-MODEL RESULT:

$$\text{Linear: } \mathbf{p}^{(1)} = \frac{q \mathbf{E} e^{-i\omega t}}{k/m - \omega^2 - i\Gamma\omega} = \alpha^{(1)} \cdot \mathbf{E}$$

$$\text{2nd-order: } \mathbf{p}^{(2)} = \frac{q \kappa_2 \Delta \mathbf{x}_1^2}{k/m - 4\omega^2 - 2i\Gamma\omega} = \alpha^{(2)} \cdot \mathbf{E} \mathbf{E}$$

where $\alpha^{(1)}$ and $\alpha^{(2)}$ are the polarizability and hyperpolarizability, respectively.

SIMPLIFIED BOND HYPERPOLARIZABILITY MODEL

- (1) Charge is localized in bonds j with directions $\hat{\mathbf{b}}_j$
- (2) Charge driven by external field results in dipoles \mathbf{p}_j
- (3) Dipoles radiate according to standard dipole-radiation relation
- (4) The only relevant motion for SHG is that along the bond axis, equivalent to assuming cylindrical symmetry
- (5) The bond directions $\hat{\mathbf{b}}_j$ are those of the bulk material.

GENERAL SBHM FAR-FIELD EXPRESSIONS:

Linear:

$$\mathbf{E}^{(1)} \sim [\mathbf{I} - \hat{\mathbf{k}}\hat{\mathbf{k}}] \cdot [\sum_j \alpha_j^{(1)} \hat{\mathbf{b}}_j \hat{\mathbf{b}}_j] \cdot \mathbf{E}_{\text{inc}}$$

SHG:

$$\mathbf{E}^{(2)} \sim [\mathbf{I} - \hat{\mathbf{k}}\hat{\mathbf{k}}] \cdot [\sum_j \alpha_j^{(2)} \hat{\mathbf{b}}_j \hat{\mathbf{b}}_j \hat{\mathbf{b}}_j] \cdot \mathbf{E}_{\text{inc}} \mathbf{E}_{\text{inc}}$$

These are simple enough to solve analytically for low-index surfaces.

for the p-p case:

$$\begin{aligned}\vec{E}_{ff} = & [\hat{x}\cos\beta + \hat{z}\sin\beta] [\alpha_u \sin^2\alpha \sin\beta \\ & + \alpha_d (\cos^3\theta \sin^2\alpha \sin\beta + \frac{3}{4} \sin\theta \sin 2\theta (\cos^2\alpha \sin\beta \\ & - \sin 2\alpha \cos\beta) + \frac{3}{4} \sin^3\theta \cos^2\alpha \cos\beta \cos 3\phi)];\end{aligned}\quad (8a)$$

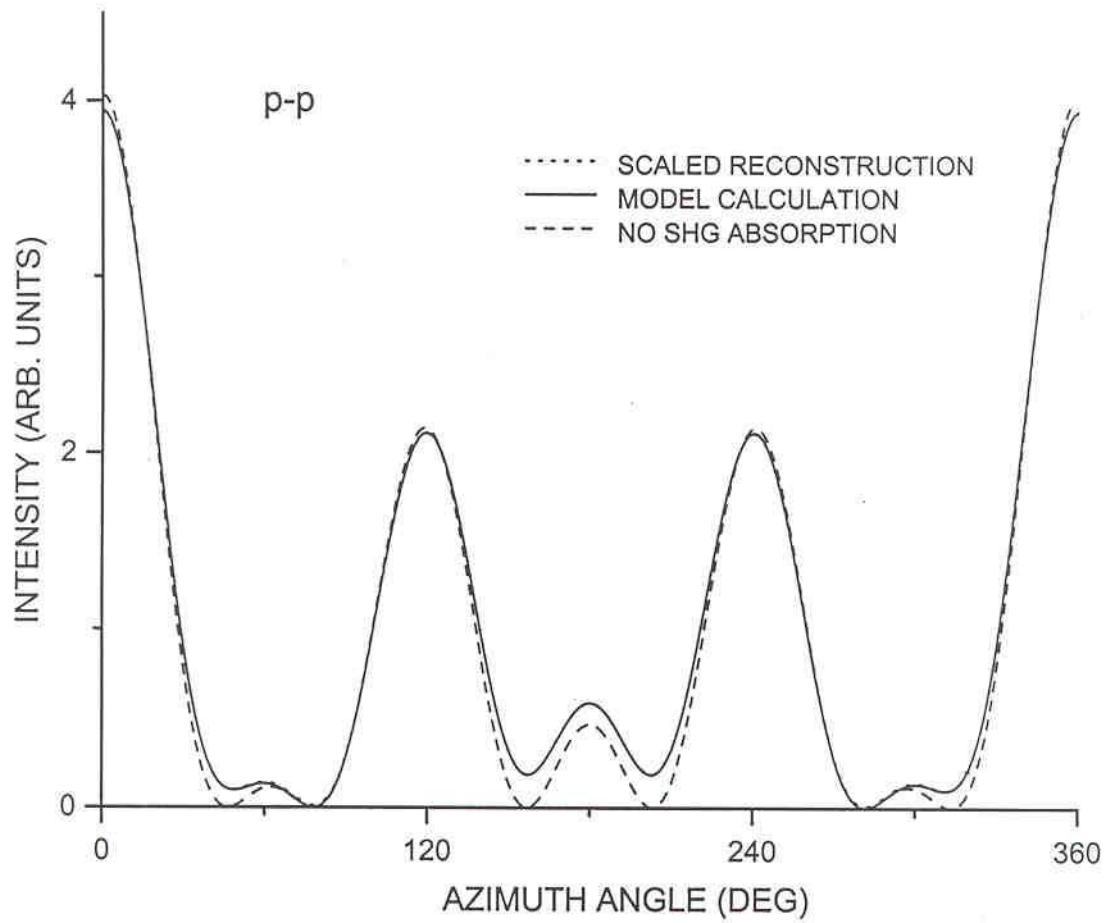
for the p-s case:

$$\vec{E}_{ff} = \hat{y} \frac{3}{4} \alpha_d \sin^3\theta \cos^2\alpha \sin 3\phi;\quad (8b)$$

CRITICAL TESTS:

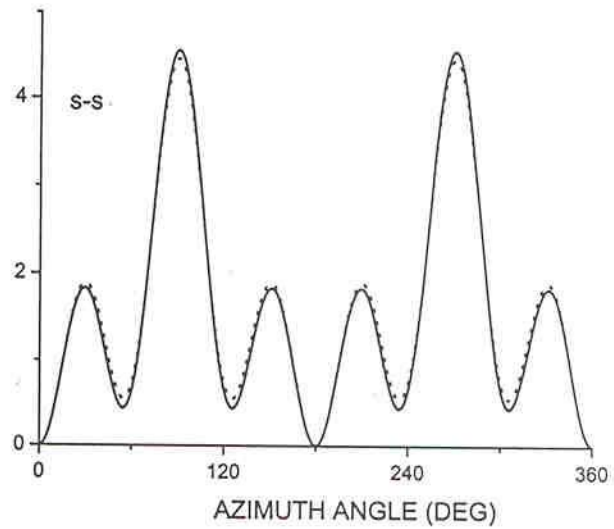
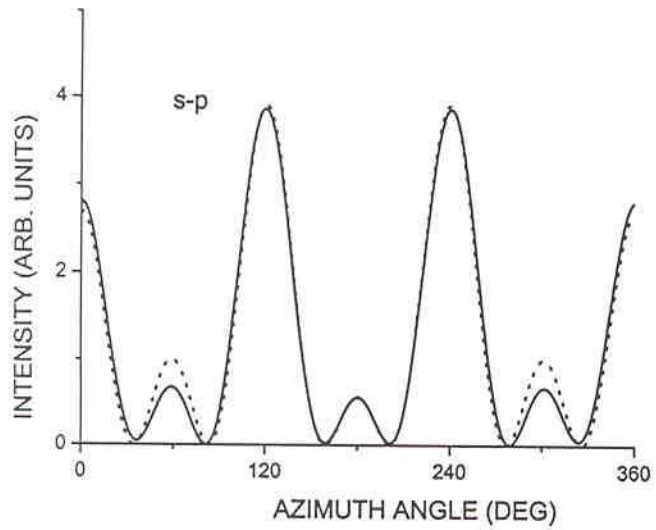
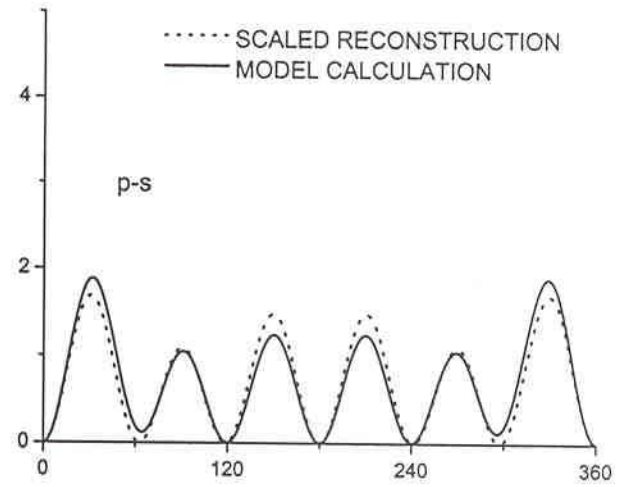
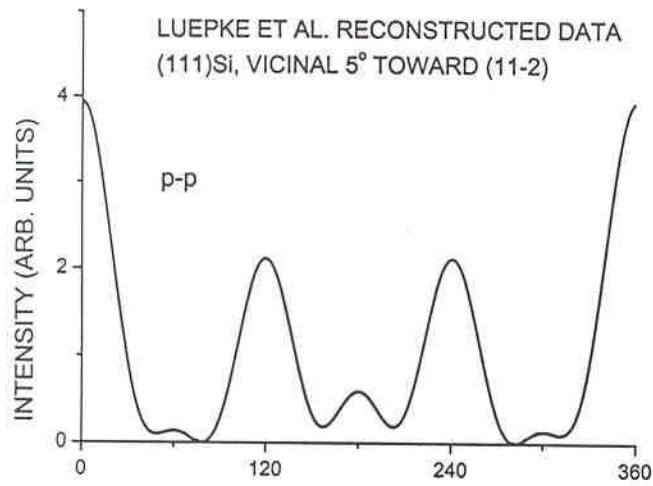
Use Lüpke et al. oxidized 5° vicinal (111)Si data:

- All four configurations pp, ps, sp, ss are available
- Amplitudes normalized to 3ϕ field (6ϕ intensity) component, automatically taking Fresnel factors into account



HYPERPOLARIZABILITIES FOR p-p, (111) Si/SiO₂:

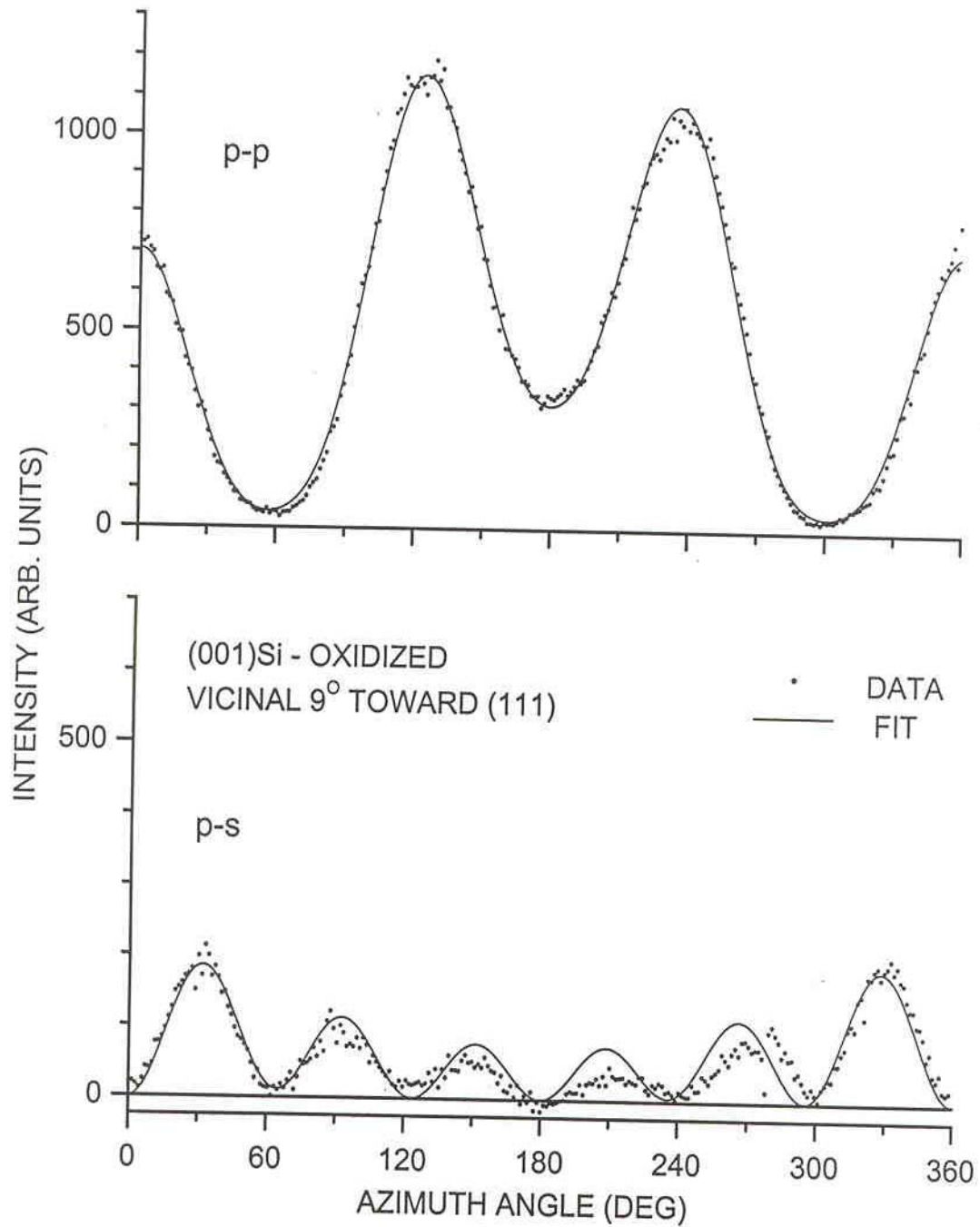
Bond:	Re	Im
Up:	1.78	0.15
Step:	2.76	1.42
Back 1:	2.19	-0.01
Back 2:	2.19	-0.01



SCALING FACTORS FOR p-s, s-p, s-s:

	Exp.	Theor.	θ
p-p	1.00 (ref.)	1	...
p-s	1.40	$1/\cos^2 \theta$	32.5°
s-p	1.93	$1/\cos^4 \theta$	32.0°
s-s	2.26	$1/\cos^6 \theta$	29.2°

Snell's Law at air-SiO₂ interface: 29.0°



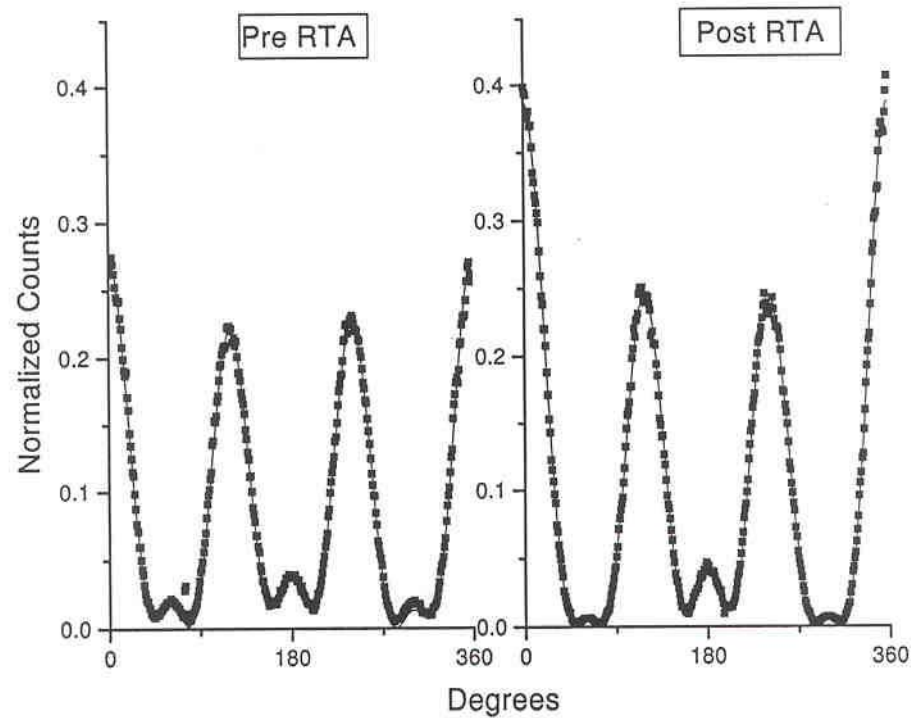
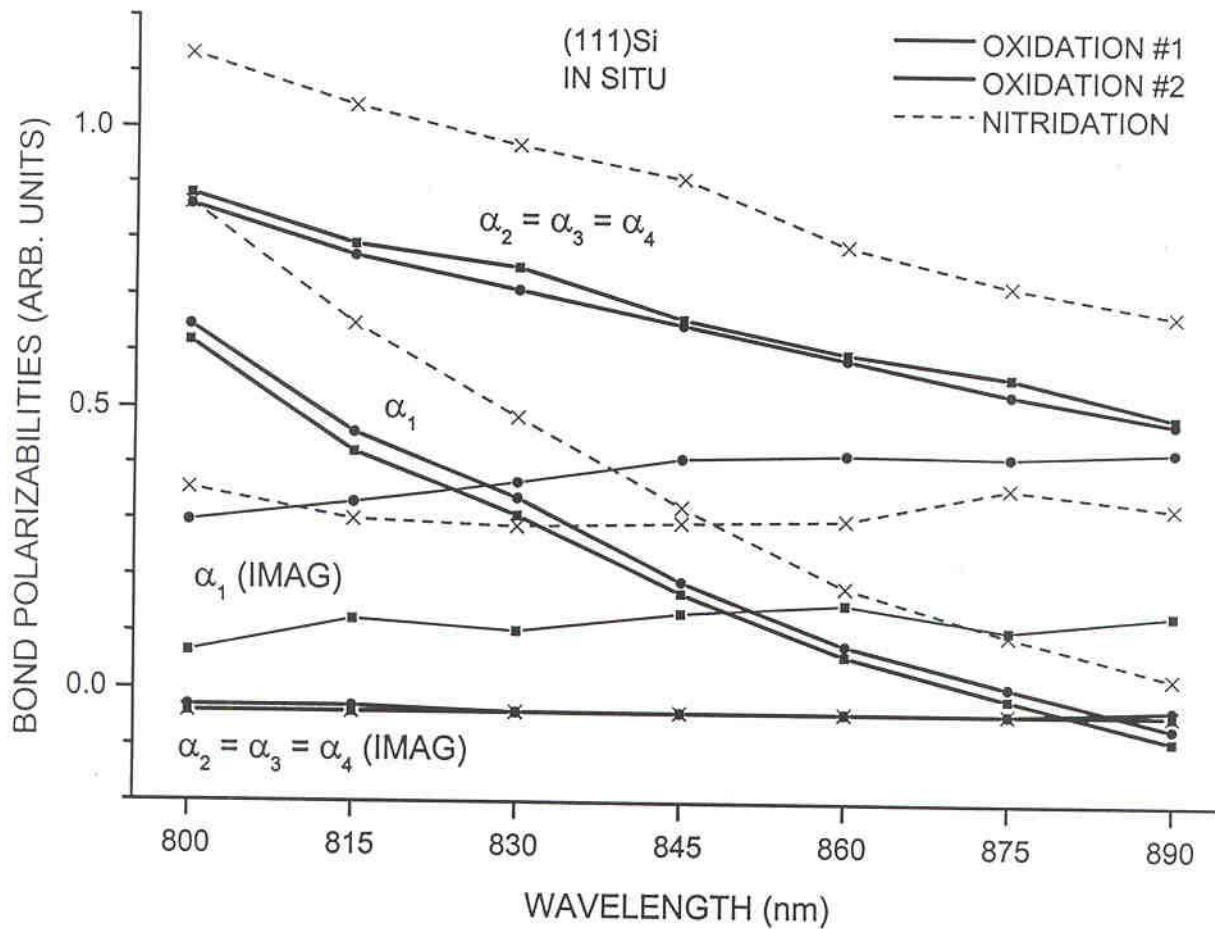


Figure 3.6: Example ex-situ SHG anisotropies and phenomenological fits at 830nm for vicinal (111) Si cut 5° toward $(11\bar{2})$ with oxidation and oxide cap before and after RTA.



CONCLUSIONS:

- (1) The SBHM enormously simplifies the analysis of SHG data relative to previous methods
- (2) It also provides insights at the microscopic level (complex hyperpolarizabilities of specific bonds) as well as SHG mechanisms (effective angles of incidence, origin of SHG signals)
- (3) We obtain consistent descriptions of pp, ps, sp, and ss data where available
- (4) We conclude that in many if not most cases SHG is actually simpler than linear optics
- (5) Next step: spectral responses...
- (6) ...followed, we believe, by renewed interest in the use of SHG as a diagnostic probe.